HFZT

SD101CWS

Schottky Barrier Diode

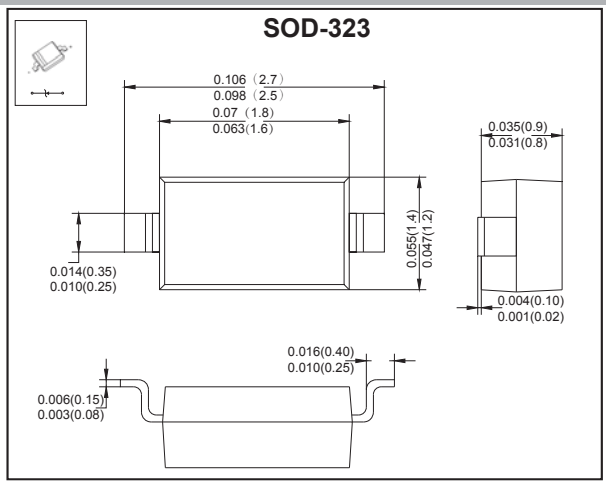
VOLTAGE RANGE: 40V **PEAK PULSE POWER:200mW**

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient
- Protection Negligible Reverse Recovery Time

MECHANICAL DATA

- Case: SOD-323 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous Current	I_{FM}	15	mA
Non-Repetitive Peak Forward Surge Current @t=8. .3ms	I_{FSM}	2.0	A
Power Dissipation	Pd	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Junction temperature	T_j	125	℃
Storage Temperature	T_{STG}	-55~+150	℃

Electrical Specification (T_A=25@25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	40			V	I_R=10μA
Forward voltage	V_F			0.39 0.90	V	I_F=1.0mA I_F=15mA
Reverse current	I_R			0.2	μA	V_R=30V
Capacitance between terminals	C_T		2.2		pF	V_R=0V,f=1.0MHz
Reverse recovery time	t_{rr}			1.0	ns	I_F=I_R=5mA I_{rr}=0.1XI_R,R_L=100Ω

MARKING: S3

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics